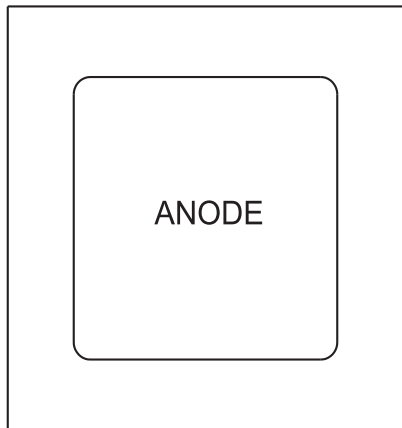


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14 X 14 MILS
Die Thickness	7.5 MILS
Anode Bonding Pad Area	9.5 X 9.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 14,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 4 INCH WAFER

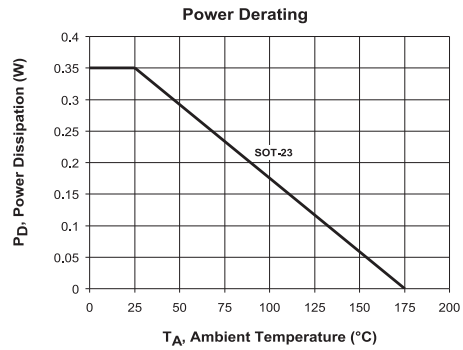
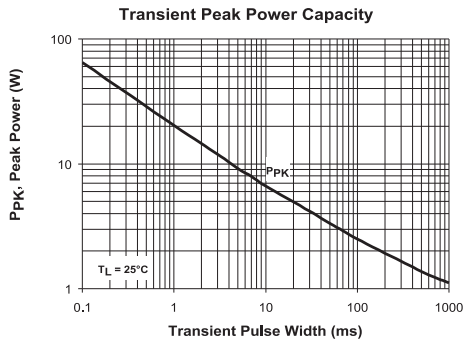
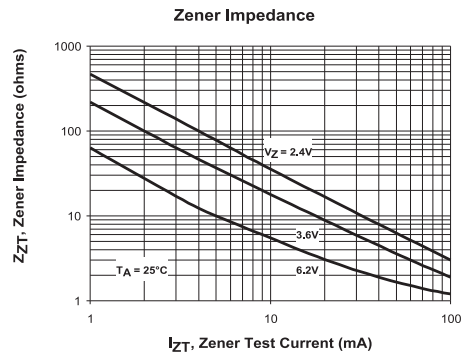
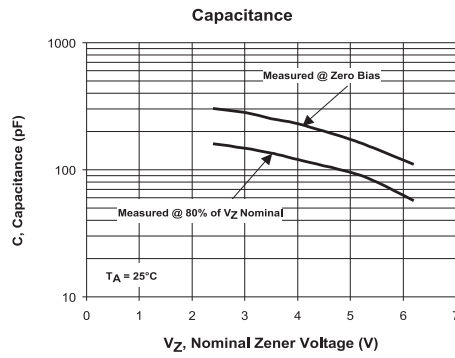
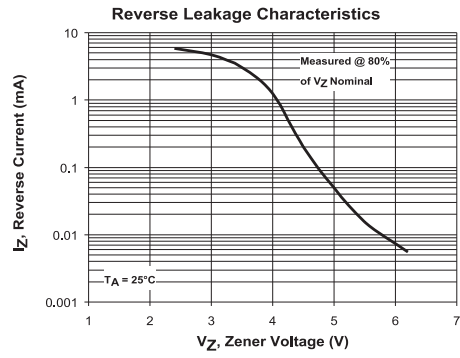
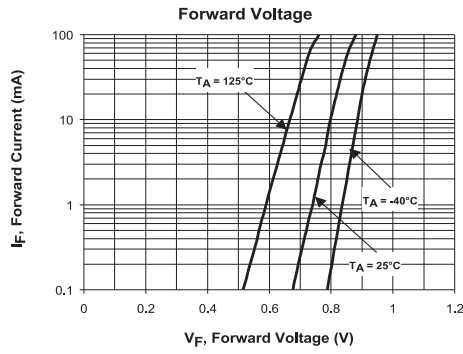
61,141

PRINCIPAL DEVICE TYPES

CMPZ5221B
THRU
CMPZ5234B

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